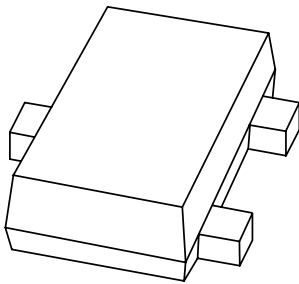


DATA SHEET



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PESDxS2UQ series Double ESD protection diodes in SOT663 package

Product specification
Supersedes data of 2003 Dec 15

2004 Apr 27

Double ESD protection diodes in SOT663 package

PESDxS2UQ series

FEATURES

- Uni-directional ESD protection of up to two lines
- Max. peak pulse power: $P_{pp} = 150 \text{ W}$ at $t_p = 8/20 \mu\text{s}$
- Low clamping voltage: $V_{(CL)R} = 20 \text{ V}$ at $I_{pp} = 15 \text{ A}$
- Low reverse leakage current: $I_{RM} < 1 \text{ nA}$
- ESD protection $> 30 \text{ kV}$
- IEC 61000-4-2; level 4 (ESD)
- IEC 61000-4-5 (surge); $I_{pp} = 15 \text{ A}$ at $t_p = 8/20 \mu\text{s}$.

APPLICATIONS

- Computers and peripherals
- Communication systems
- Audio and video equipment
- High speed data lines
- Parallel ports.

DESCRIPTION

Uni-directional double ESD protection diodes in a SOT663 plastic package. Designed to protect up to two transmission or data lines from ElectroStatic Discharge (ESD) damage.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾
PESD3V3S2UQ	*E1
PESD5V0S2UQ	*E2
PESD12VS2UQ	*E3
PESD15VS2UQ	*E4
PESD24VS2UQ	*E5

Note

1. * = p : made in Hong Kong.
 * = t : made in Malaysia.
 * = W : made in China.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	VALUE	UNIT
V_{RWM}	reverse stand-off voltage	3.3, 5, 12, 15 and 24	V
C_d	diode capacitance $V_R = 0 \text{ V};$ $f = 1 \text{ MHz}$	200, 150, 38, 32 and 23	pF
	number of protected lines	2	

PINNING

PIN	DESCRIPTION
1	cathode 1
2	cathode 2
3	common anode

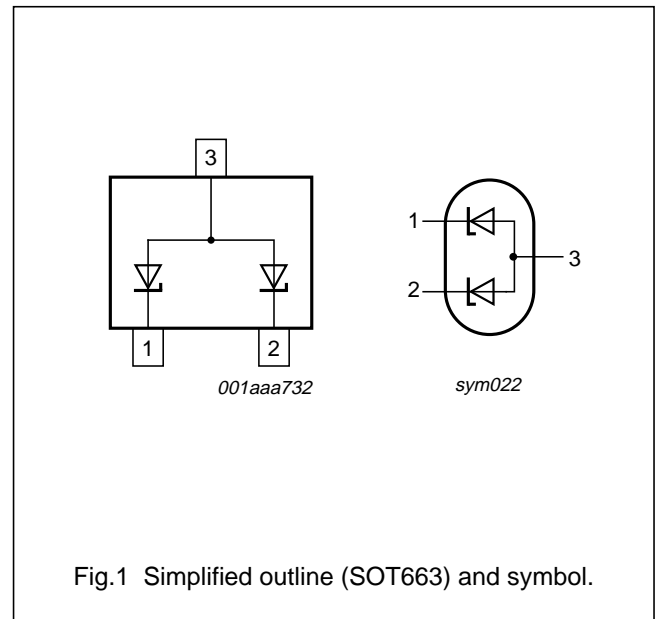


Fig.1 Simplified outline (SOT663) and symbol.

Double ESD protection diodes in SOT663 package

PESDxS2UQ series

ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PESD3V3S2UQ	-	plastic surface mounted package; 3 leads	SOT663
PESD5V0S2UQ			
PESD12VS2UQ			
PESD15VS2UQ			
PESD24VS2UQ			

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT			
P_{pp}	peak pulse power	8/20 μ s pulse; notes 1 and 2	-	150	W			
I_{pp}	peak pulse current	8/20 μ s pulse; notes 1 and 2						
	PESD3V3S2UQ					-	15	A
	PESD5V0S2UQ					-	15	A
	PESD12VS2UQ					-	5	A
	PESD15VS2UQ					-	5	A
	PESD24VS2UQ	-	3	A				
T_j	junction temperature		-	150	$^{\circ}$ C			
T_{amb}	operating ambient temperature		-65	+150	$^{\circ}$ C			
T_{stg}	storage temperature		-65	+150	$^{\circ}$ C			

Notes

1. Non-repetitive current pulse 8/20 μ s exponential decaying waveform; see Fig.2.
2. Measured across either pins 1 and 3 or pins 2 and 3.

Double ESD protection diodes in SOT663 package

PESDxS2UQ series

ESD maximum ratings

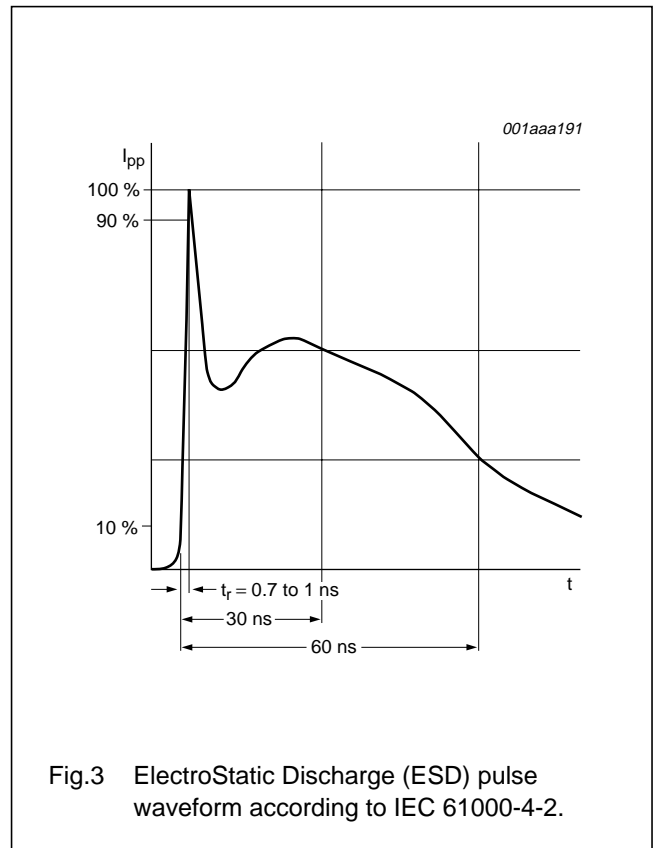
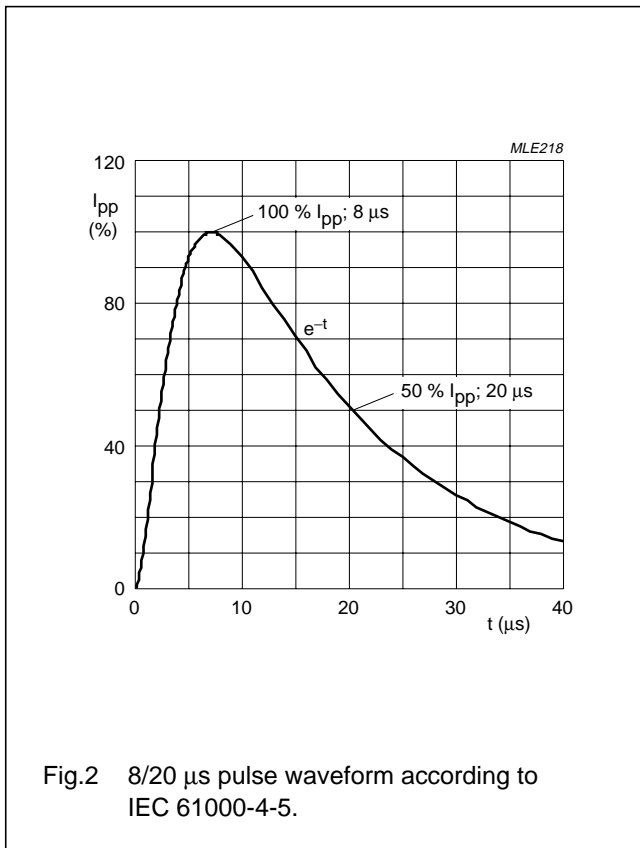
SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
ESD	electrostatic discharge capability	IEC 61000-4-2 (contact discharge); notes 1 and 2		
		PESD3V3S2UQ	30	kV
		PESD5V0S2UQ	30	kV
		PESD12VS2UQ	30	kV
		PESD15VS2UQ	30	kV
		PESD24VS2UQ	23	kV
	HBM MIL-Std 883 PESDxS2UQ series	10	kV	

Notes

1. Device stressed with ten non-repetitive ElectroStatic Discharge (ESD) pulses; see Fig.3.
2. Measured across either pins 1 and 3 or pins 2 and 3.

ESD standards compliance

ESD STANDARD	CONDITIONS
IEC 61000-4-2; level 4 (ESD); see Fig.3	>15 kV (air); > 8 kV (contact)
HBM MIL-Std 883; class 3	>4 kV



Double ESD protection diodes in SOT663 package

PESDxS2UQ series

ELECTRICAL CHARACTERISTICS

$T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{RWM}	reverse stand-off voltage					
	PESD3V3S2UQ		–	–	3.3	V
	PESD5V0S2UQ		–	–	5	V
	PESD12VS2UQ		–	–	12	V
	PESD15VS2UQ		–	–	15	V
	PESD24VS2UQ		–	–	24	V
I_{RM}	reverse leakage current					
	PESD3V3S2UQ	$V_{RWM} = 3.3\text{ V}$	–	0.55	3	μA
	PESD5V0S2UQ	$V_{RWM} = 5\text{ V}$	–	50	300	nA
	PESD12VS2UQ	$V_{RWM} = 12\text{ V}$	–	<1	30	nA
	PESD15VS2UQ	$V_{RWM} = 15\text{ V}$	–	<1	50	nA
	PESD24VS2UQ	$V_{RWM} = 24\text{ V}$	–	<1	50	nA
V_{BR}	breakdown voltage	$I_Z = 5\text{ mA}$				
	PESD3V3S2UQ		5.2	5.6	6.0	V
	PESD5V0S2UQ		6.4	6.8	7.2	V
	PESD12VS2UQ		14.7	15.0	15.3	V
	PESD15VS2UQ		17.6	18.0	18.4	V
	PESD24VS2UQ		26.5	27.0	27.5	V
C_d	diode capacitance	$f = 1\text{ MHz}; V_R = 0\text{ V}$				
	PESD3V3S2UQ		–	200	275	pF
	PESD5V0S2UQ		–	150	215	pF
	PESD12VS2UQ		–	38	100	pF
	PESD15VS2UQ		–	32	70	pF
	PESD24VS2UQ		–	23	50	pF
$V_{(CL)R}$	clamping voltage	notes 1 and 2				
	PESD3V3S2UQ	$I_{pp} = 1\text{ A}$	–	–	8	V
		$I_{pp} = 15\text{ A}$	–	–	20	V
	PESD5V0S2UQ	$I_{pp} = 1\text{ A}$	–	–	9	V
		$I_{pp} = 15\text{ A}$	–	–	20	V
	PESD12VS2UQ	$I_{pp} = 1\text{ A}$	–	–	19	V
		$I_{pp} = 5\text{ A}$	–	–	35	V
	PESD15VS2UQ	$I_{pp} = 1\text{ A}$	–	–	23	V
		$I_{pp} = 5\text{ A}$	–	–	40	V
	PESD24VS2UQ	$I_{pp} = 1\text{ A}$	–	–	36	V
		$I_{pp} = 3\text{ A}$	–	–	70	V

Double ESD protection diodes in SOT663 package

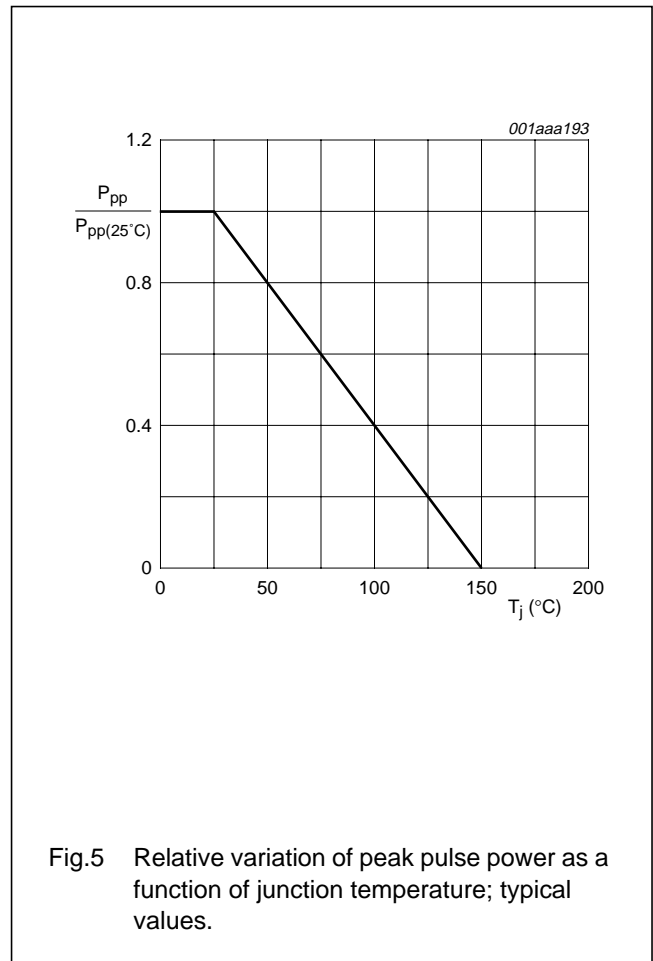
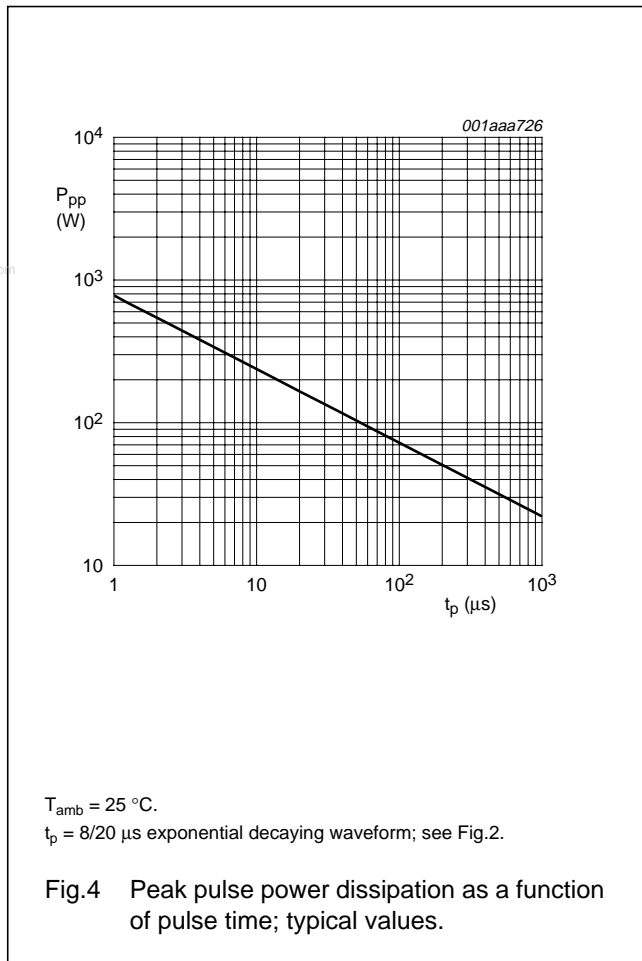
PESDxS2UQ series

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R_{diff}	differential resistance					
	PESD3V3S2UQ	$I_R = 5 \text{ mA}$	–	–	40	Ω
	PESD5V0S2UQ	$I_R = 5 \text{ mA}$	–	–	15	Ω
	PESD12VS2UQ	$I_R = 5 \text{ mA}$	–	–	15	Ω
	PESD15VS2UQ	$I_R = 1 \text{ mA}$	–	–	225	Ω
	PESD24VS2UQ	$I_R = 0.5 \text{ mA}$	–	–	300	Ω

Notes

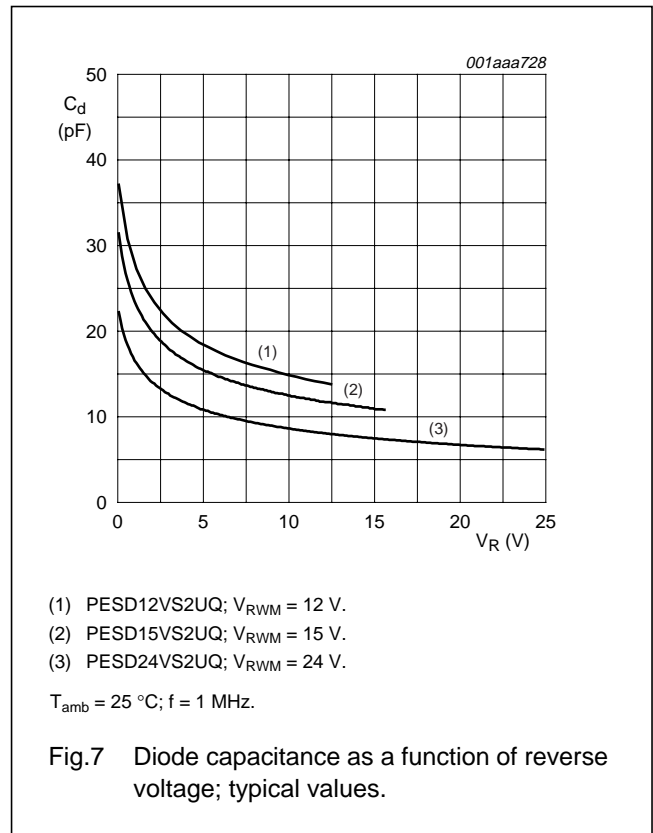
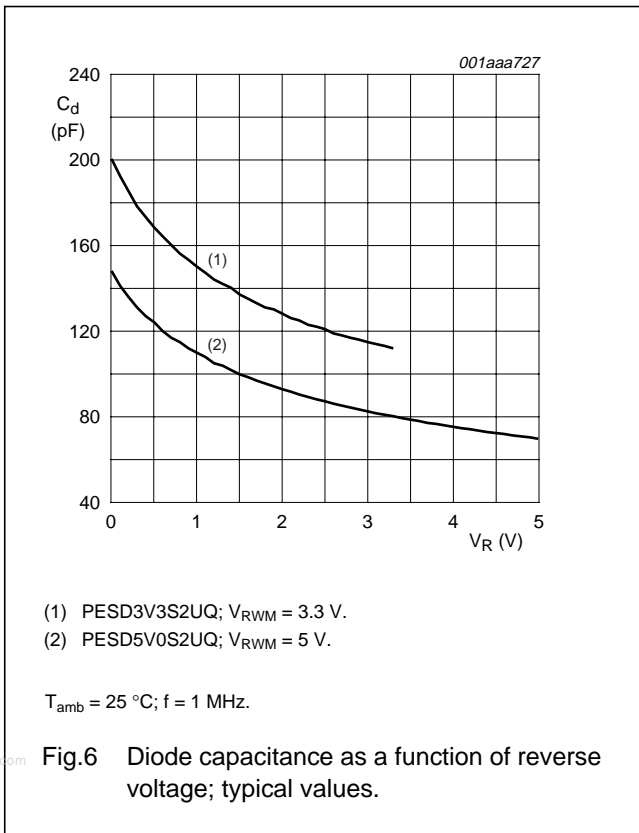
1. Non-repetitive current pulse 8/20 μs exponential decay waveform; see Fig.2.
2. Measured either across pins 1 and 3 or pins 2 and 3.

GRAPHICAL DATA



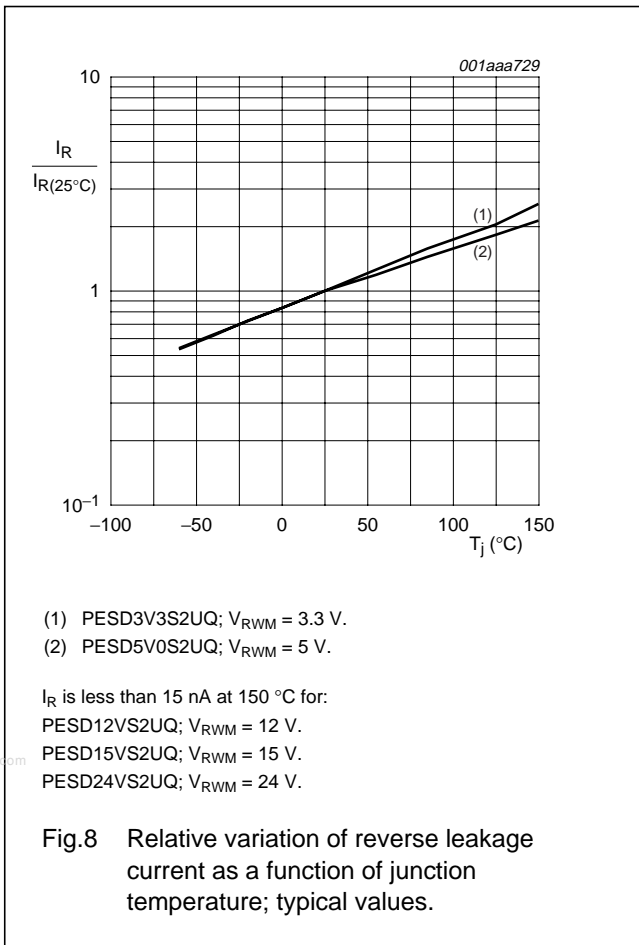
Double ESD protection diodes
in SOT663 package

PESDxS2UQ series



Double ESD protection diodes
in SOT663 package

PESDxS2UQ series



Double ESD protection diodes in SOT663 package

PESDxS2UQ series

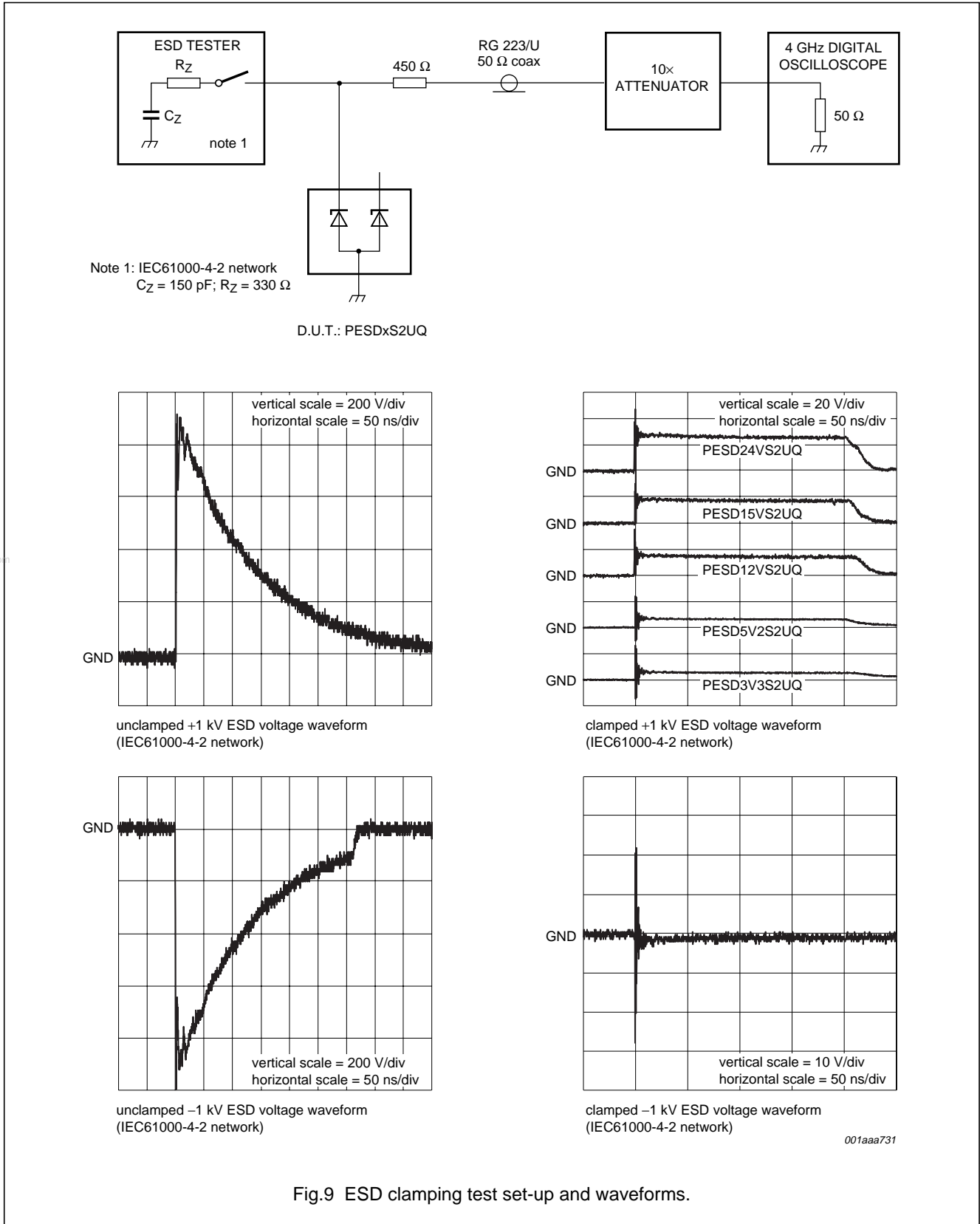


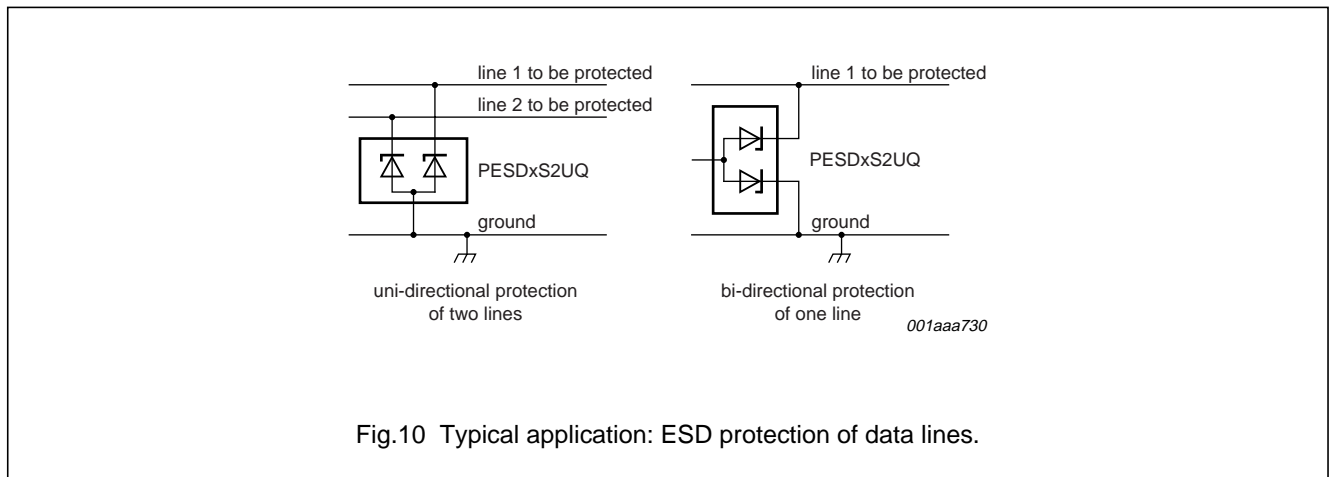
Fig.9 ESD clamping test set-up and waveforms.

Double ESD protection diodes in SOT663 package

PESDxS2UQ series

APPLICATION INFORMATION

The PESDxS2UQ series is designed for uni-directional protection for up to two data lines against damage caused by ElectroStatic Discharge (ESD) and surge pulses. The PESDxS2UQ series may be used on lines where the signal polarities are below ground. PESDxS2UQ series provide a surge capability of up to 150 W (P_{pp}) per line for an 8/20 μ s waveform.



Circuit board layout and protection device placement

Circuit board layout is critical for the suppression of ESD, Electrical Fast Transient (EFT) and surge transients. The following guidelines are recommended:

- Place the PESDxS2UQ as close as possible to the input terminal or connector.
- The path length between the PESDxS2UQ and the protected line should be minimized.
- Keep parallel signal paths to a minimum.
- Avoid running protected conductors in parallel with unprotected conductors.
- Minimize all printed-circuit board conductive loops including power and ground loops.
- Minimize the length of transient return paths to ground.
- Avoid using shared return paths to a common ground point.
- Ground planes should be used whenever possible. For multilayer printed-circuit boards use ground vias.

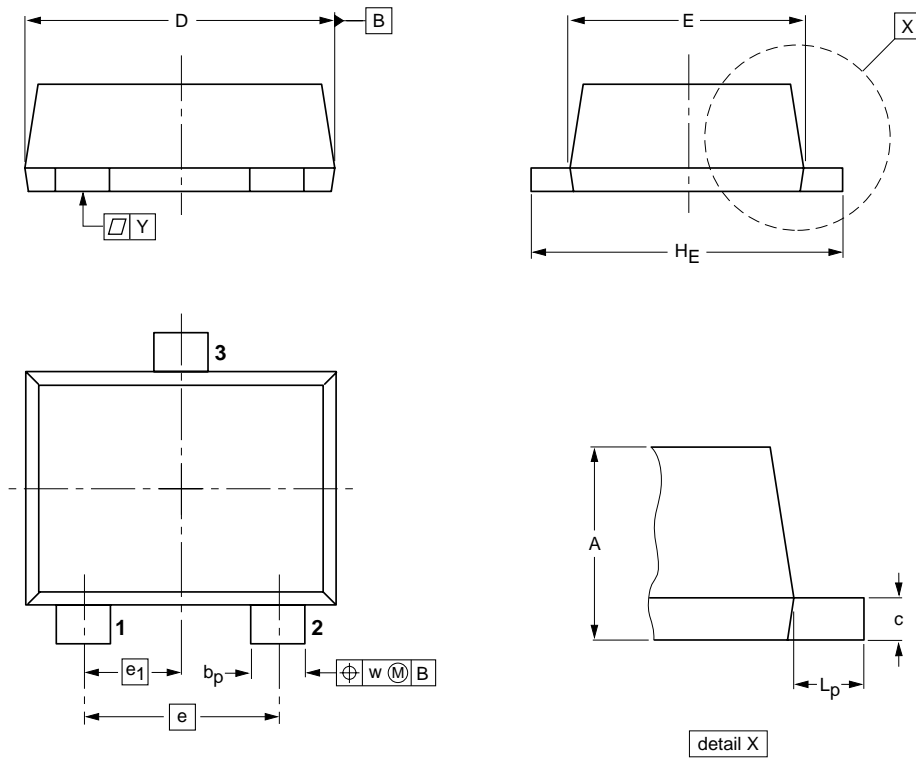
Double ESD protection diodes in SOT663 package

PESDxS2UQ series

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT663



DIMENSIONS (mm are the original dimensions)

UNIT	A	b_p	c	D	E	e	e_1	H_E	L_p	w	y
mm	0.6 0.5	0.33 0.23	0.18 0.08	1.7 1.5	1.3 1.1	1.0	0.5	1.7 1.5	0.3 0.1	0.1	0.1

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT663					01-12-04 02-05-21

Double ESD protection diodes in SOT663 package

PESDxS2UQ series

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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